





DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Up To 3KV
- Lead Free By Design/RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

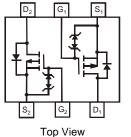
- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

SOT563









Top View

Bottom View

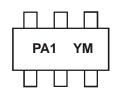
Ordering Information (Note 3)

Part Number	Case	Packaging
DMG1023UV-7	SOT563	3,000 / Tape & Reel
DMG1023UV-13	SOT563	10,000 / Tape & Reel

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free.

2. Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com

Marking Information



PA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	20	10	2011	2012	2013	2014	20	15	2016	2017
Code	V	W)	Κ	Υ	Z	Α	В	(С	D	Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

^{3.} For packaging details, go to our website at http://www.diodes.com.



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	±6	V
Continuous Drain Current (Note 4) V _{GS} = -4.5V	I _D	-1.03 -0.68	А
Pulsed Drain Current (Note 5)	I _{DM}	-3	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P_{D}	530	mW
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 4)	R _{0JA}	235	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

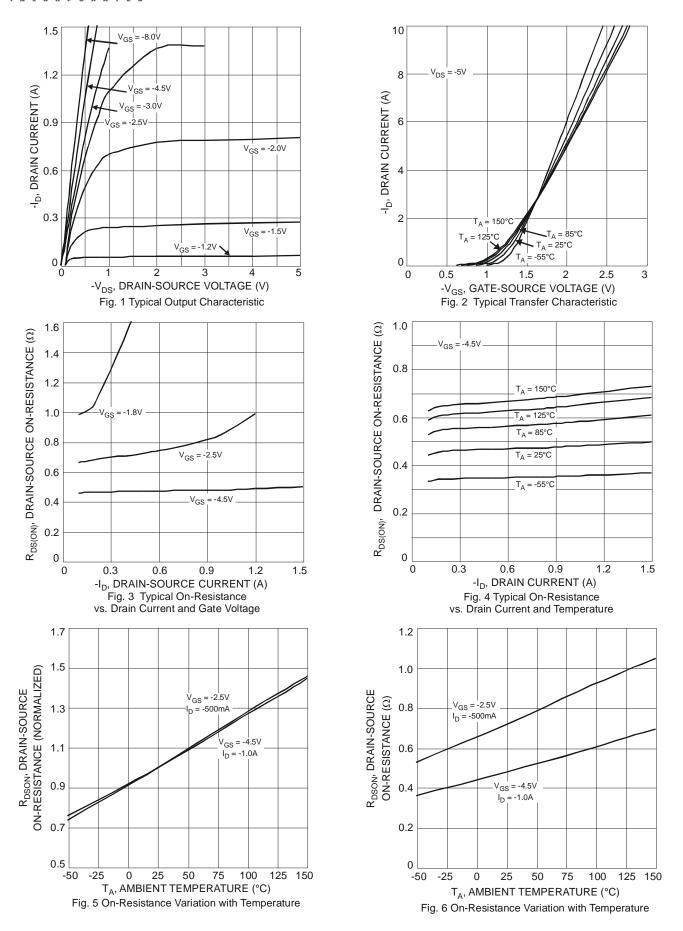
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Tym	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)	Symbol	IVIIII	Тур	IVIAX	Unit	rest Condition
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	_	-100	nA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage		_	_	±2.0	μA	$V_{GS} = \pm 4.5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)	I _{GSS}			±2.0	μΛ	VGS = ±4.5V, VDS = 0V
Gate Threshold Voltage	V _{GS(th)}	-0.5	l -	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Cate Thiodheld Voltage	V G3(III)	0.0	0.5	0.75	•	$V_{GS} = -4.5V$, $I_D = -430mA$
			0.7	1.05		$V_{GS} = -2.5V$, $I_D = -300$ mA
Static Drain-Source On-Resistance	P== (=+)	_	1.0	1.5	Ω	$V_{GS} = -1.8V$, $I_D = -150$ mA
Static Dialit-Source Off-Nesistance	R _{DS} (ON)	_	1.0	20		, -
			-	25		$V_{GS} = -1.7V, I_D = -100mA$
5 JT (A) W			-	25		$V_{GS} = -1.5V, I_{D} = -100mA$
Forward Transfer Admittance	Y _{fs}	-	0.9	-	S	$V_{DS} = -10V, I_{D} = -250mA$
Diode Forward Voltage	V_{SD}		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	59.76	-	pF	101/1/
Output Capacitance	Coss	-	12.07	-	pF	$V_{DS} = -16V, V_{GS} = 0V,$ -f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	-	6.36	-	pF	1 = 1:0\vii 12
Total Gate Charge	Qq	-	622.4	-	рC	151/1/ 101/
Gate-Source Charge	Qgs	-	100.3	-	рС	$V_{GS} = -4.5V, V_{DS} = -10V,$
Gate-Drain Charge	Q _{qd}	-	132.2	-	рС	$I_D = -250 \text{mA}$
Turn-On Delay Time	t _{D(on)}	-	5.1	-	ns	
Turn-On Rise Time	t _r	-	8.1	-	ns	V _{DD} = -10V, V _{GS} = -4.5V,
Turn-Off Delay Time	t _{D(off)}	-	28.4	-	ns	$R_L = 47\Omega, R_G = 10\Omega,$ $R_D = -200 \text{mA}$
Turn-Off Fall Time	t _f	-	20.7	-	ns	200ΠΑ

Notes:

- 4. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 5. Repetitive rating, pulse width limited by junction temperature.6. Short duration pulse test used to minimize self-heating effect.7. Guaranteed by design. Not subject to production testing.







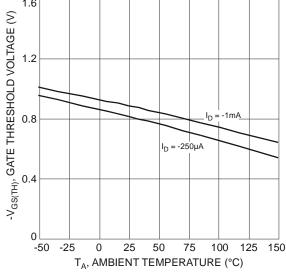
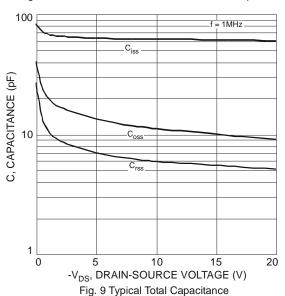
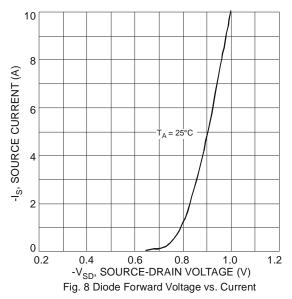


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





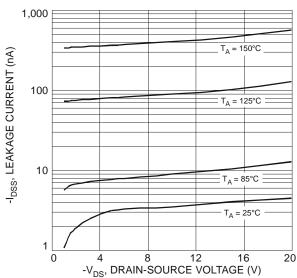


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

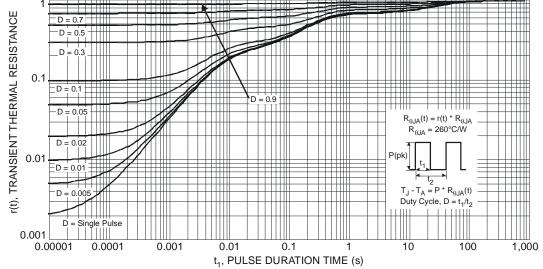
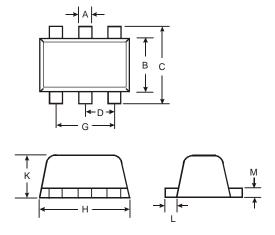


Fig. 11 Transient Thermal Response

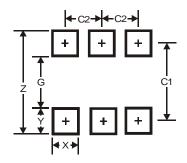


Package Outline Dimensions



SOT563							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.20				
В	1.10	1.25	1.20				
С	1.55	1.70	1.60				
D	•	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
K	K 0.55 0.60 0.60						
L	0.10	0.30	0.20				
М	0.10	0.18	0.11				
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5



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